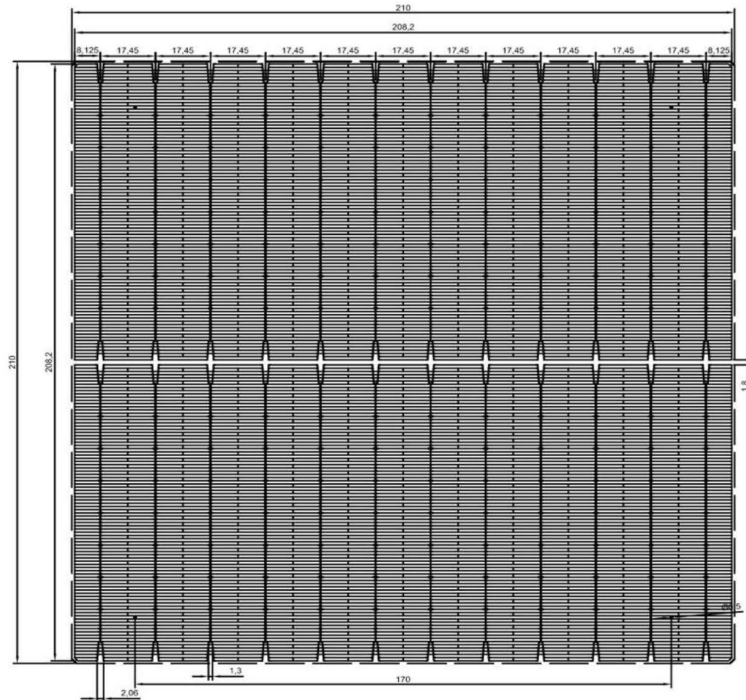


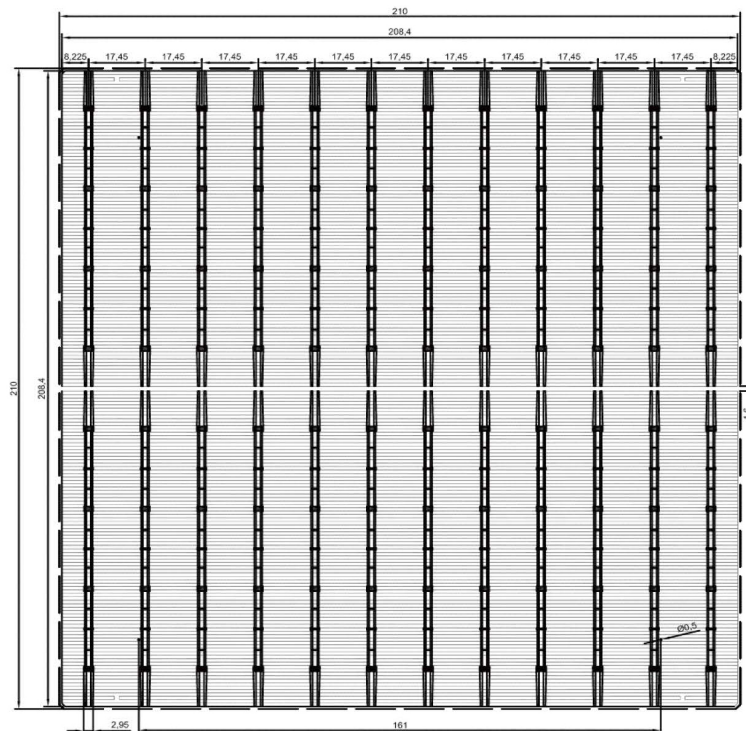


Technical Specification

• 技术图形 Technical drawing



Front



Back



• 电气特性 Electrical Characteristics

Grade	Eff(%)	Pmpp(W)	Vmpp(V)	Impp(A)	Voc(V)	Isc(A)	FF(%)
1	23.2	10.23	0.605	16.913	0.696	17.776	82.74
2	23.1	10.19	0.604	16.868	0.695	17.733	82.69
3	23.0	10.14	0.603	16.848	0.694	17.715	82.61
4	22.9	10.1	0.602	16.816	0.694	17.662	82.55
5	22.8	10.05	0.601	16.751	0.693	17.642	82.42
6	22.7	10.01	0.599	16.749	0.692	17.612	82.34
7	22.6	9.97	0.597	16.718	0.691	17.585	82.22
8	22.5	9.92	0.595	16.679	0.690	17.556	82.01
9	22.4	9.88	0.593	16.669	0.688	17.539	81.93
10	22.3	9.83	0.592	16.635	0.688	17.529	81.70
11	22.2	9.79	0.591	16.582	0.684	17.479	81.68
12	22.1	9.75	0.589	16.558	0.684	17.458	81.67

标准测试条件下(Under standard test condition):1000W/m², AM1.5, 25°C

温度系数 Temperature coefficients

开路电压温度系数 Temperature coefficients of open circuit voltage: -0.36%/K

短路电流温度系数 Temperature coefficients of short circuit current: +0.07%/K

最大功率温度系数 Temperature coefficients of maximum power: -0.38%/K

• 机械特征 Mechanical characteristics

尺寸规格 **Dimension:** 210mmx210mm±0.25mm; 电池厚度 **Cell Thickness:** 180±10μm

正面(一) **Front side:** 二氧化硅+深蓝色氮化硅复合减反膜(PID Free); 主栅宽度: 0.1±0.05mm; 主栅头部呈双叉, 186根副栅线, 正电极为半片设计。

Silicon oxide+blue silicon nitride compound anti-reflection coating(PID Free);The width of the busbar is 0.1±0.05mm;the head of the busbar is forked;the number of the finger is 186;The front side of solar cell is designed as a half sheet.

背面(十) **Back side:** 钝化发射极(氧化铝及氮化硅复合层); 背电极宽度为 2.1±0.1mm, 12根主栅线(铝), 186根副栅线(铝)
Passivated Emitter (AlOx and SiNx dual layer) rear contact;The width and length of the Ag electrode is 2.1±0.1mm, the number of the aluminum busbar is 12; the number of the aluminum finger is 186;

可焊性 (**Solderability**): 最小剥离强度 (Peel strength) ≥1.0N/mm

结果可能会因焊条、焊接方法及条件而不同。Results may vary depending on the conditions.